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APPLICATION NO.	FILING DATE	. FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
09/273,784	03/22/1999	JOHN G. MCBRIDE	10971308-1	7570
22879	7590 11/04/2002			
HEWLETT PACKARD COMPANY P O BOX 272400, 3404 E. HARMONY ROAD INTELLECTUAL PROPERTY ADMINISTRATION			EXAMINER	
			PHAN, THAI Q	
FORT COLLINS, CO 80527-2400			ART UNIT	PAPER NUMBER
			2123	

DATE MAILED: 11/04/2002

Please find below and/or attached an Office communication concerning this application or proceeding.



Office Action Summary

Application No. 09/273,784

Applicant(s)

John McBride

Examiner

Thai Phan

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	The MAILING DATE of this communication appears of	on the cover s	heet with	the correspondence address			
	or Reply						
THE	ORTENED STATUTORY PERIOD FOR REPLY IS SET MAILING DATE OF THIS COMMUNICATION. Ions of time may be available under the provisions of 37 CFR 1.136 (a). In n						
mailing - If the p - If NO p - Failure - Any re	date of this communication. period for reply specified above is less than thirty (30) days, a reply within the period for reply is specified above, the maximum statutory period will apply ar to reply within the set or extended period for reply will, by statute, cause the ply received by the Office later than three months after the mailing date of th patent term adjustment. See 37 CFR 1.704(b).	e statutory minimur nd will expire SIX (6 e application to bec	n of thirty (30 3) MONTHS f	D) days will be considered timely. rom the mailing date of this communication. DNED (35 U.S.C. § 133).			
Status							
1) 💢	Responsive to communication(s) filed on <u>Aug. 18, 2</u>	2002		·			
2a) 🗌	This action is FINAL . 2b) 💢 This acti	on is non-fina	al.				
3) 🗆	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11; 453 O.G. 213.						
Disposit	tion of Claims						
4) 💢	Claim(s) <u>1-20</u>			is/are pending in the application.			
4	a) Of the above, claim(s)		····-	is/are withdrawn from consideration.			
5) 🗆	Claim(s)			is/are allowed.			
	Claim(s) 1, 2, 8, 9, 15, and 16						
	Claim(s) 3-7, 10-14, and 17-20						
	Claims						
Application Papers							
9) 🗆	The specification is objected to by the Examiner.						
10)	10) ☐ The drawing(s) filed on is/are a) ☐ accepted or b) ☐ objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)	The proposed drawing correction filed on						
	If approved, corrected drawings are required in reply to this Office action.						
12) The oath or declaration is objected to by the Examiner.							
Priority under 35 U.S.C. §§ 119 and 120							
13) Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).							
a) □ All b) □ Some* c) □ None of:							
1. Certified copies of the priority documents have been received.							
	2. Certified copies of the priority documents have been received in Application No.						
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).							
	ee the attached detailed Office action for a list of the						
14) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).							
a) The translation of the foreign language provisional application has been received.							
15) Acknowledgement is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.							
Attachm		4) Interview	Summen, IPT.	O-413) Paper No(s)			
	otice of References Cited (PTO-892) otice of Draftsperson's Patent Drawing Review (PTO-948)	_	· ·	nt Application (PTO-152)			
_	3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)						
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DETAILED ACTION

This Office Action is responsive to applicant's response filed Aug. 13, 2002. Applicant's argument in the Brief for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn. Claims 1-20 are pending in this official action.

Claim Rejections - 35 USC § 101

1. Applicant's arguments with respect to claim rejection under 35 USC 101 rejection is persuasive. The rejection is thus withdraw from this Office action.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action.

A person shall be entitled to a patent unless --

- (e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371© of this title before the invention thereof by the applicant for patent.
- 3. Claims 1, 2, 8, 9, 15, and 16 are rejected under 35 U.S.C. 102(e) as being anticipated by Kochpatcharin et al., patent no. 5,844,818.

As per claims 1 and 15, Kochpatcharin anticipates method and system for design rule checking of an integrated circuit design with feature limitations as claimed (Abstract and

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Summary of the Invention). According to Kochpatcharin, the method and system for design rule checking includes a computer configured to execute a rule checker program, wherein the design rule being checked for an integrated circuit design having gates, gate connected in datapath or along circuit paths including static gate characteristics, transistor parameters such as transistor widths, lengths, connected in device channel, etc. ("Summary of the Invention", col. 6, lines 19-51, for instance). The program is designed to check transistor susceptible to noise in the cross-talk influence (col. 2, lines 7-24, col. 5, lines 18-56, col. 9, line 54 to col. 10, line 2), including checking noise susceptible or noise immunity as claimed for transistors to other transistors as claimed for design practice adherence or design quality as suggested in background of the invention.

As per claim 2, Kochpatcharin anticipate reading transistor design parameters for design rule check as claimed. Such transistor circuit design in static gate under rule checking would include for example inverter gate, p-channel and n-channel transistor, CMOS channel parameters, design parameters, etc. as well-known in transistor circuit design, and the rule checking of the gate circuit statically verifies device characteristics susceptible to noise in a specified design operation bound within thresholds values as known in MOS circuit operation (Background of the Invention).

As per claim 8, Kochpatcharin anticipates method for design rule checking of an integrated circuit design with feature limitations as claimed (Abstract and Summary of the Invention). According to Kochpatcharin, the design rule checking method includes steps for receiving gate characteristics such as width and length of the design gate parameter for static gate

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rule checking, wherein the design gate usually contained more than one field effect transistor, and the gates connected in datapath or along circuit paths including static gate characteristics in which the gate characteristics involving with transistor parameters such as transistor widths, lengths, connected in device channel, etc. ("Summary of the Invention", col. 6, lines 19-51, for instance). The rule checking method is to check transistor susceptible to noise in the cross-talk influence (col. 2, lines 7-24, col. 5, lines 18-51, col. 6, lines 20-51), including checking noise susceptible or noise immunity as claimed for transistors to other transistors as claimed for design practice adherence or design quality as suggested in background of the invention.

As per claim 9, Kochpatcharin anticipate reading transistor design parameters for design rule check as claimed. Such transistor circuit design in static gate under rule checking would include for example inverter gate, p-channel and n-channel transistor, CMOS channel parameters, design parameters, etc. as well-known in transistor circuit design, and the rule checking of the gate circuit statically verifies device characteristics susceptible to noise in a region of operation bound by threshold values as known in MOS device operation (Background of the Invention).

As per claim 16, Kochpatcharin anticipate reading transistor design parameters for design rule check as claimed. Such transistor circuit design in static gate under rule checking would include for example inverter gate, p-channel and n-channel transistor, CMOS channel parameters, design parameters, etc. as well-known in transistor circuit design, and the rule checking of the gate circuit statically verifies device characteristics susceptible to noise, namely,

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within specific design threshold values as known in MOS circuit operation (Background of the Invention).

Allowable Subject Matter

4. Claims 3-7, 10-14, and 17-20 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Dependent claims 3-7, 10-14, and 17-20 are objected to because the claims require a plurality of checking models for rule checking program and method, each rule checking model is associated with ratio of the width of the P-field transistor to the width of the N-field transistor, the ratio corresponding to the numerical value stored in the memory device. In each checking model, the rule checker program obtaining a (first) ratio of the width of the n and p-type transistor of the first model, the first ratio used to access the first and second threshold values stored in the memory device, the rule checker program determines noise levels on the inputs taking possible high or low values, and compares the determined noise levels to the first and second threshold values to determine the gate meets acceptable noise immunity requirement with respect to each model as claimed herein. The art of record does not expressly disclose such limitations as in the dependent claims.

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Response to Arguments

5. Applicant's arguments with respect to claims 1-20 have been considered but are moot in view of a new ground of rejection.

Any inquiry of a general nature or relating to the status of this application should be directed to the Group receptionist whose telephone number is (703)305-3900.

Any response to this action should be mailed to:

Commissioner of Patents and Trademarks

Washington, D.C. 20231

or faxed to:

(703) 746-7239, (for formal communications intended for entry)

Or:

(703) 746-7240 (for informal or draft communications, please label

"PROPOSED" or "DRAFT")

Hand-delivered responses should be brought to Crystal Park II, 2121 Crystal Drive, Arlington. VA., Sixth Floor (Receptionist).

October 28, 2002

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